

Vishay High Power Products

FlipKY[®], 1 A



FlipKY[®]

FEATURES

- Ultra low V_F per footprint area
- Low thermal resistance
- One-fifth footprint of SMA
- Super low profile (< 0.7 mm)
- Available tested on tape and reel
- Small footprint, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead (Pb)-free
- Designed for consumer level

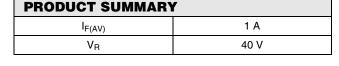
DESCRIPTION

True chip-scale packaging is available from Vishay HPP. The FCSP140TR surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

The FlipKY[®] package, is one-fifth the footprint of a comparable SMA package and has a profile of less then 0.7 mm. Combined with the low thermal resistance of the die level device, this makes the FlipKY the best device for applications where printed circuit board space is at a premium and in extremely thin application environments such as battery packs, cell phones and PCMCIA cards.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
l _F	Rectangular waveform	1.0	А		
V _{RRM}		40	V		
I _{FSM}	$t_p = 5 \ \mu s \ sine$	250	А		
V _F	1.0 Apk, T _J = 125 °C	0.38	V		
TJ	Range	- 55 to 150	°C		

VOLTAGE RATINGS					
PARAMETER	SYMBOL	FCSP140TR	UNITS		
Maximum DC reverse voltage	V _R	40	V		
Maximum working peak reverse voltage	V _{RWM}	40	v		





OMPLIANT

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	I _{F(AV)}	50 % duty cycle at T_{PCB} = 112 °C, rectangular waveform		1.0	
Maximum peak one cycle non-repetitive surge current at 25 °C	I	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with	250	A
	IFSM	10 ms sine or 6 ms rect. pulse	rated V _{RRM} applied	21	
Non-repetitive avalanche energy	E _{AS}	$T_J = 25 \text{ °C}, I_{AS} = 2.0 \text{ A}, L = 5.0 \text{ mH}$		10	mJ
Repetitive avalanche current	I _{AR}	$\begin{array}{c} \mbox{Current decaying linearly to zero in 1 } \mu \mbox{s} \\ \mbox{Frequency limited by } T_J \mbox{ maximum } V_A = 1.5 \mbox{ x } V_R \mbox{ typical} \end{array} \end{array} \end{tabular}$		2.0	А

ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum forward voltage drop See fig. 1	V _{EM} ⁽¹⁾	1 A	T _J = 25 °C	0.43	0.48	V
		2 A		0.51	0.56	
	V FM (")	1 A	T _ 105 °C	0.34	0.38	
		2 A	T _J = 125 °C	0.46	0.53	
Maximum reverse leakage current See fig. 2		V _R = Rated V _R		10 3.5 2	80	μΑ
		V _R = 20 V	T ₁ = 25 °C		20	
		V _R = 10 V	- 1j=25 C	2	10	
	I _{RM} ⁽¹⁾	V _R = 5 V		9.0 20 3.5 8	5	
	IRM (17	V _R = Rated V _R			20	
		V _R = 20 V	T _J = 125 °C		8	mA
		V _R = 10 V	- 1j = 125 C		6	
		V _R = 5 V		2	5	
Maximum junction capacitance	CT	V_{R} = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		-	160	pF
Maximum voltage rate of change	dV/dt	Rated V _R		-	10 000	V/µs

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J ⁽¹⁾ , T _{Stg}		- 55 to 150	°C	
Typical thermal resistance junction to PCB	R _{thJL} ⁽²⁾	DC operation	40	°C/W	
Typical thermal resistance junction to ambient	R _{thJA}		62	0/₩	

Notes

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

(2) Mounted on 1" square PCB



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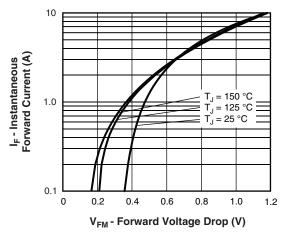
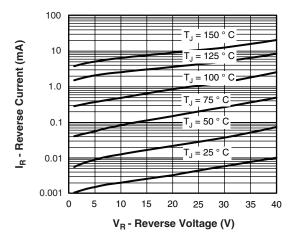
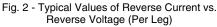
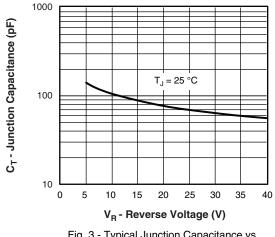
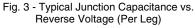


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)









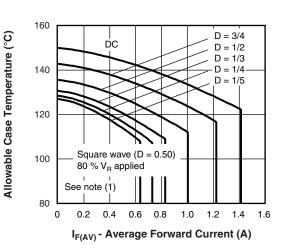


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

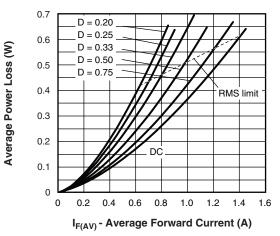
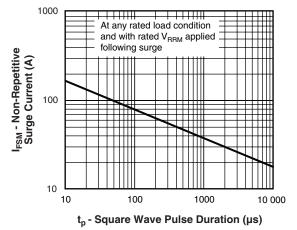


Fig. 5 - Forward Power Loss Characteristics (Per Leg)





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at 80 % V_R applied

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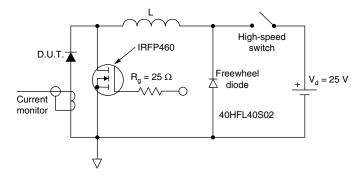


Fig. 7 - Unclamped Inductive Test Circuit

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95052			
Part marking information	http://www.vishay.com/doc?95281			
Packaging information	http://www.vishay.com/doc?95062			



Vishay

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